

MAIL STOP PCT

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Docket No. 291520US0PCT



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Kazuhito YASUDA, et al.

SERIAL NO: 10/580,833

GAU:

FILED: May 26, 2006

EXAMINER:

FOR: SEMICONDUCTOR RADIATION DETECTOR AND PROCESS FOR PRODUCING THE SAME

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- The applicant(s) wish to make of record the references cited in the International Search Report and listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- Attached is a list of applicant's pending application(s), published application(s) or issued patent(s) which may be related to the present application. In accordance with the waiver of 37 CFR 1.98 dated September 21, 2004, copies of the cited pending applications are not provided. Cited published and/or issued patents, if any, are listed on the attached PTO form 1449.
- A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- Each item of information contained in this information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

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SHEET 1 OF 1

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 291520US0PCT	SERIAL NO. 10/580,833		
LIST OF REFERENCES CITED BY APPLICANT		APPLICANT Kazuhito YASUDA, et al.					
		FILING DATE May 26, 2006		GROUP			
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
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FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION		
					YES	NO	
	AO						
	AP						
	AQ						
	AR						
	AS						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
AT	NAKANISHI, Yutaro et al., "Growth and Electronic Properties of Thick CdTe Layers Grown on GaAs by MOVPE", Technical Report of IEICE., Vol. 103, No. 50, pgs. 81-85, 2003.						
AU	MASUDA, Yusuke et al., "Arsenic Doping in CdTe Layers Grown by Metalorganic Vapor Phase Epitaxy", Technical Report of IEICE., Vol. 101, No. 82, pgs. 13-18, 2001.						
AV	YASUDA, K. et al., "MOVPE growth of (100) CdZnTe Layers Using DiPZn", Journal of Crystal Growth, Vol. 159, pgs. 121-125. 1996.						
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AX	WANG, Wen-Sheng et al., "(100) or (111) Heterohepitaxy of CdTe Layers on (100) GaAs Substrates by Organometallic Vapor Phase Epitaxy", Materials Chemistry and Physics, Vol. 51, pgs. 178-181, 1997.						
AY	LEO, G. et al., "Influence of a ZnTe Buffer Layer on the Structural Quality of CdTe Epilayers Grown on (100) GaAs by Metalorganic Vapor Phase Epitaxy", J.Vac.Technol.B., Vol. 14, No. 3, pgs 1739-1744, 1996.						
AZ					<input type="checkbox"/> Additional References sheet(s) attached		
Examiner					Date Considered		
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							